



HI-SINCERITY MICROELECTRONICS CORP.

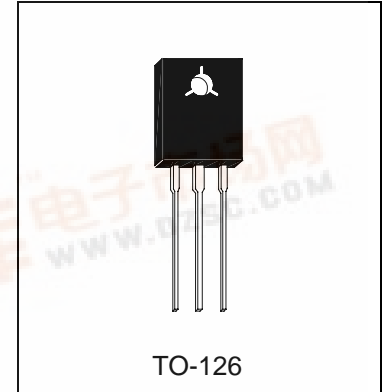
Spec. No. : HT200101
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HT112

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HT112 is designed for use in general purpose amplifier and low-speed switching applications.



Absolute Maximum Ratings (T_A=25°C)

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (T_A=25°C) 1.5 W
 - Total Power Dissipation (T_C=25°C) 30 W
- Thermal Resistance
 - Junction To Case R_{θjc} 4.2 °C/W
- Maximum Voltages and Currents
 - BV_{CBO} Collector to Base Voltage 100 V
 - BV_{CEO} Collector to Emitter Voltage 100 V
 - BV_{EBO} Emitter to Base Voltage 5 V
 - I_C Collector Current 4 A

Electrical Characteristics (T_A=25°C)

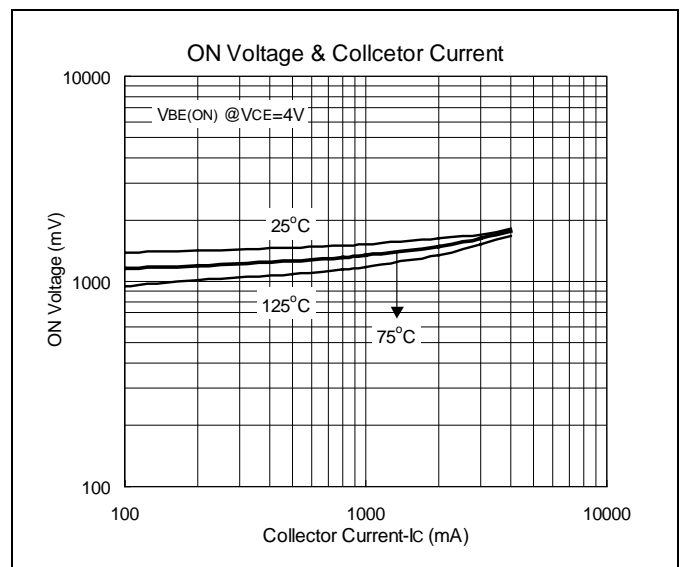
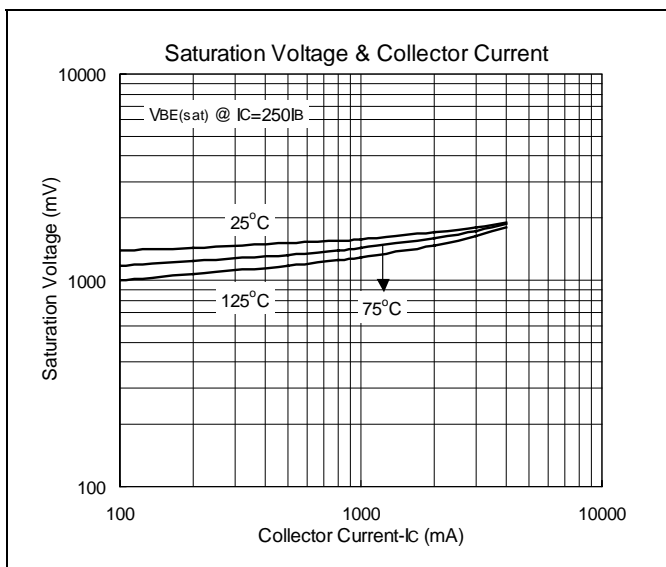
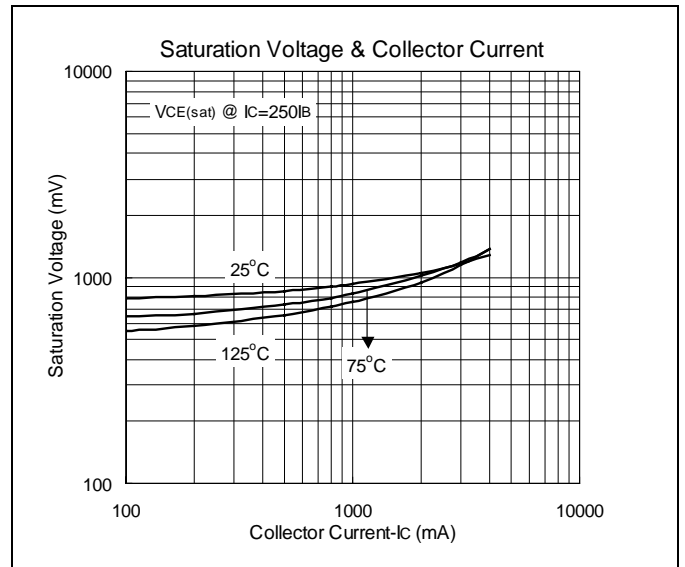
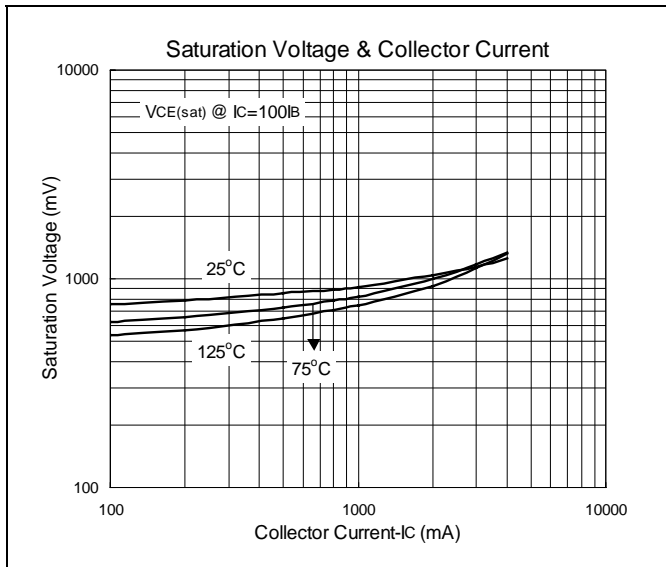
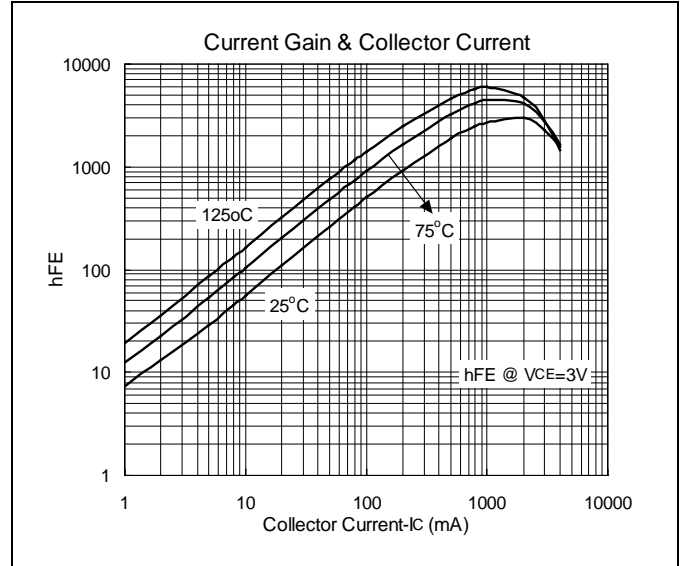
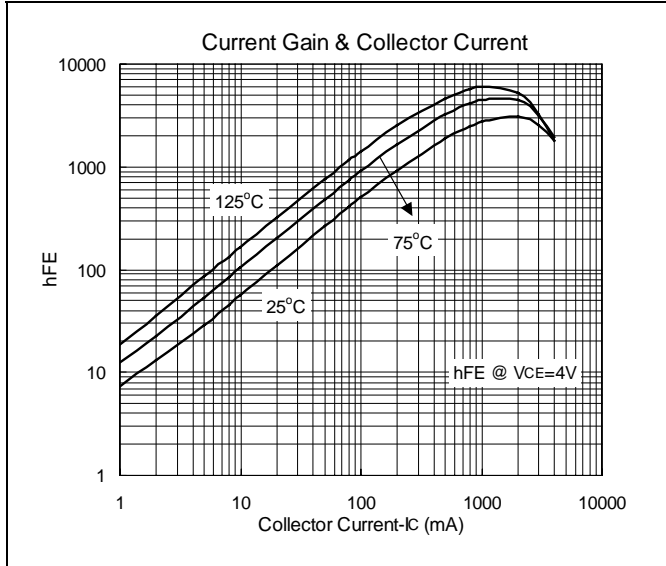
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	100	-	-	V	I _C =1mA
BV _{CEO}	100	-	-	V	I _C =30mA
I _{CBO}	-	-	1	mA	V _{CB} =100V
I _{CEO}	-	-	2	mA	V _{CE} =50V
I _{EBO}	-	-	2	mA	V _{EB} =5V
*V _{CE(sat)}	-	-	2.5	V	I _C =2A, I _B =8mA
*V _{BE(on)}	-	-	2.8	V	I _C =2A, V _{CE} =4V
*h _{FE1}	1	-	-	K	I _C =1A, V _{CE} =4V
*h _{FE2}	500	-	-		I _C =2A, V _{CE} =4V
Cob	-	-	100	pF	V _{CB} =10V, I _E =0

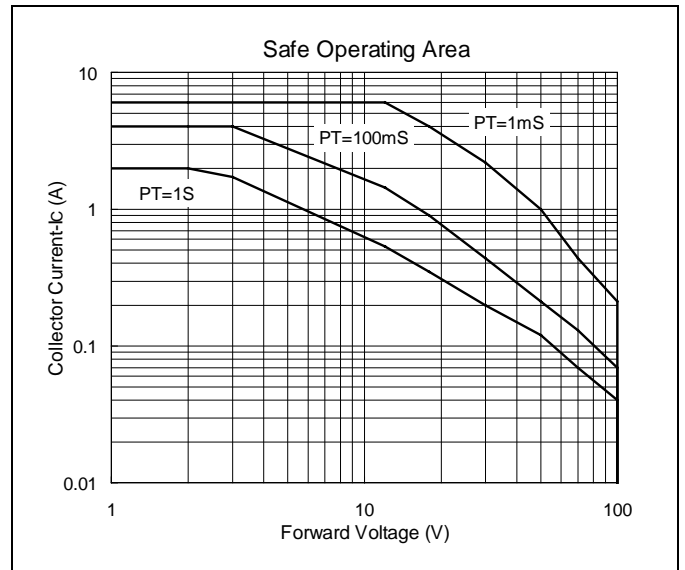
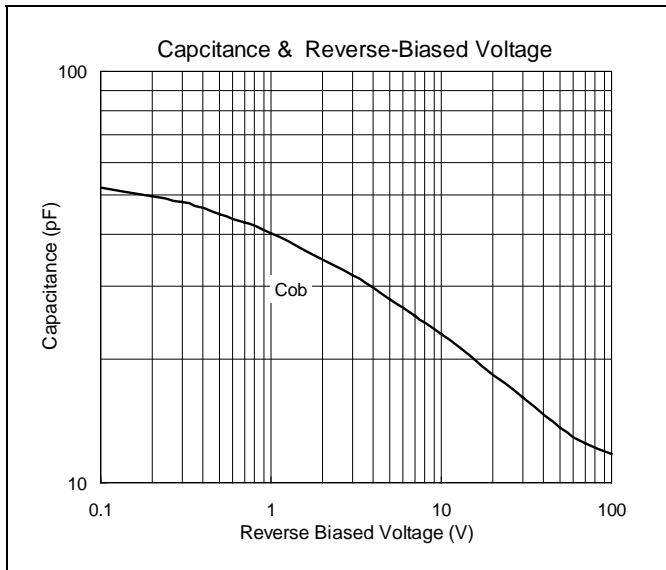
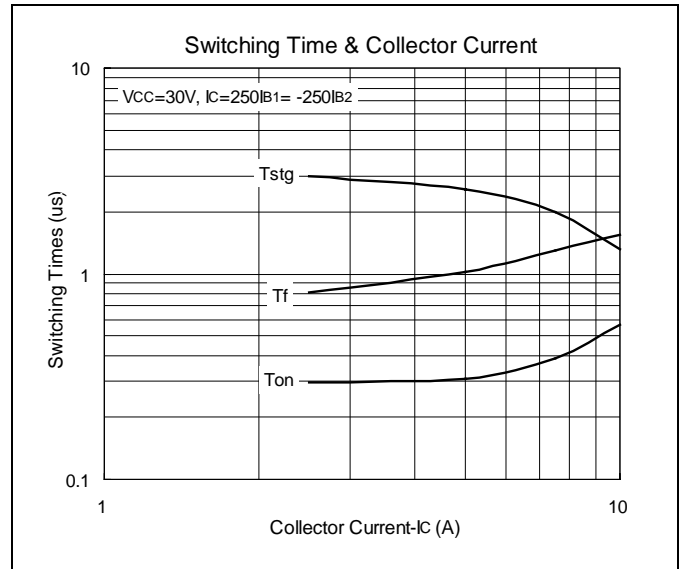
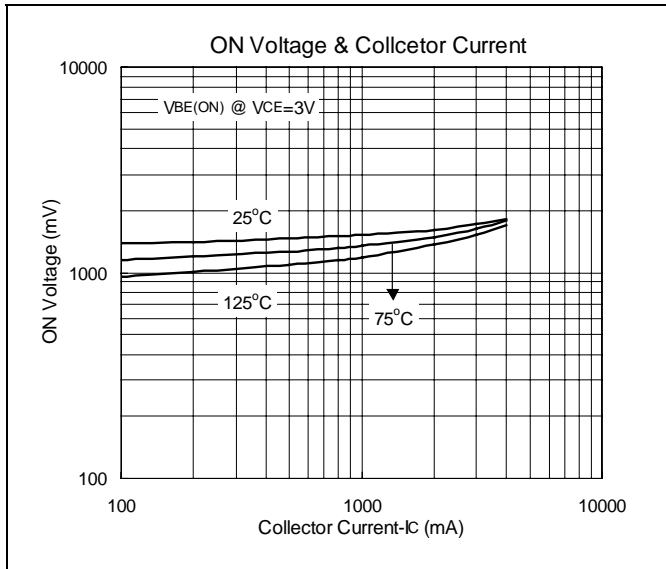
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%





Characteristics Curve







TO-126 Dimension

3-Lead TO-126
Plastic Package
HSMC Package Code: T

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing
 Pin Style: 1.Emitter 2.Collector 3.Base

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	3.60	4.40
B	6.90	7.60
C	13.00	16.50
D	7.20	8.50
F	0.65	0.88
G	1.00	1.42
H	4.52	4.62
J	1.14	1.50
K	0.90	1.50
L	0.45	0.60
M	2.92	3.40
N	2.00	2.70

Unit: mm

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Head Office And Factory:

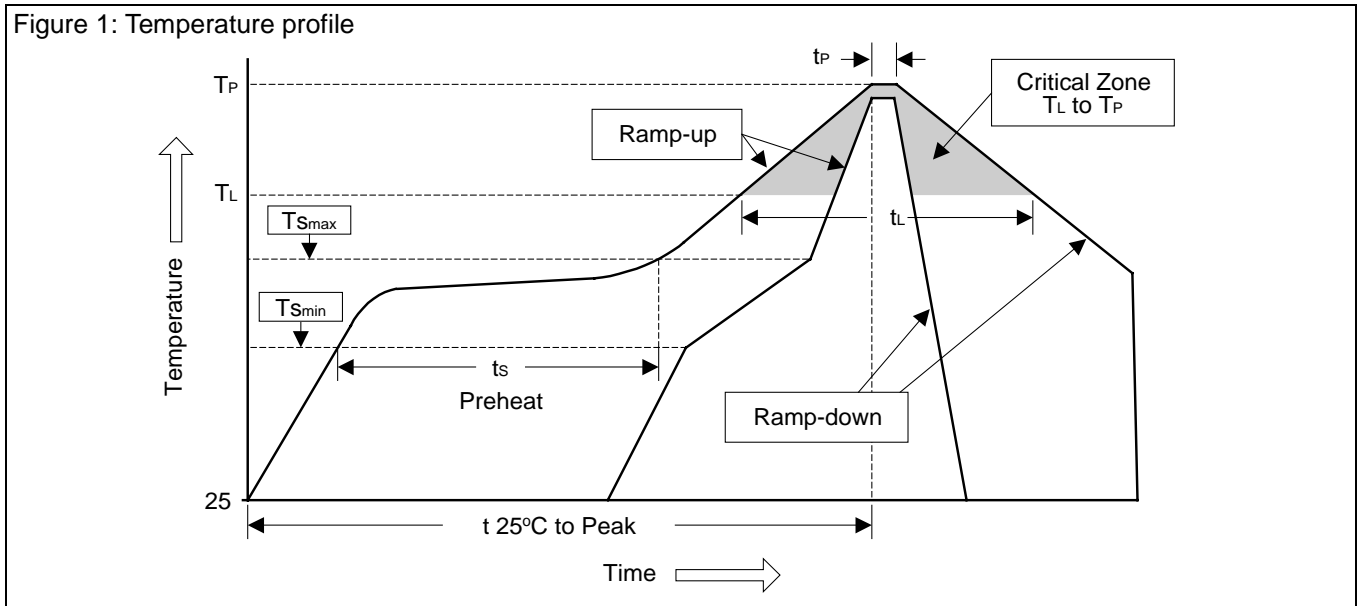
- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
 Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
 Tel: 886-3-5983621~5 Fax: 886-3-5982931



Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec